



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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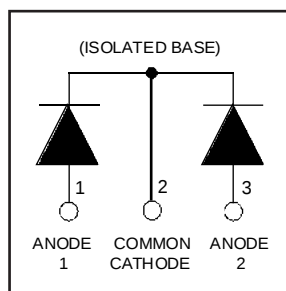
HFA60MC60C

HEXFRED™

Ultrafast, Soft Recovery Diode

Features

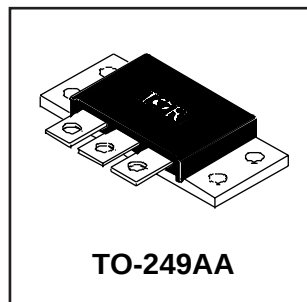
- Reduced RFI and EMI
- Reduced Snubbing
- Extensive Characterization of Recovery Parameters



$V_R = 600V$
$V_F(\text{typ.})^{③} = 1.1V$
$I_{F(AV)} = 60A$
$Q_{rr}(\text{typ.}) = 200nC$
$I_{RRM}(\text{typ.}) = 6A$
$t_{rr}(\text{typ.}) = 30ns$
$di_{(rec)}/dt(\text{typ.})^{③} = 170A/\mu s$

Description

HEXFRED™ diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and di/dt simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.



Absolute Maximum Ratings (per Leg)

	Parameter	Max.	Units
V_R	Cathode-to-Anode Voltage	600	V
$I_F @ T_C = 25^\circ C$	Continuous Forward Current	50	A
$I_F @ T_C = 100^\circ C$	Continuous Forward Current	24	
I_{FSM}	Single Pulse Forward Current ①	200	
E_{AS}	Non-Repetitive Avalanche Energy ②	220	μJ
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	125	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	50	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	$^\circ C$
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	

Thermal - Mechanical Characteristics

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case, Single Leg Conducting	—	—	1.0	$^\circ C/W$ K/W
	Junction-to-Case, Both Legs Conducting	—	—	0.50	
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	—	0.10	—	
Wt	Weight	—	58 (2.0)	—	g (oz)
	Mounting Torque	35 (4.0)	—	50 (5.7)	lbf•in (N•m)

Note: ① Limited by junction temperature

② $L = 100\mu H$, duty cycle limited by max T_J

③ $125^\circ C$

HFA60MC60C

PD-2.463 rev. B 03/99

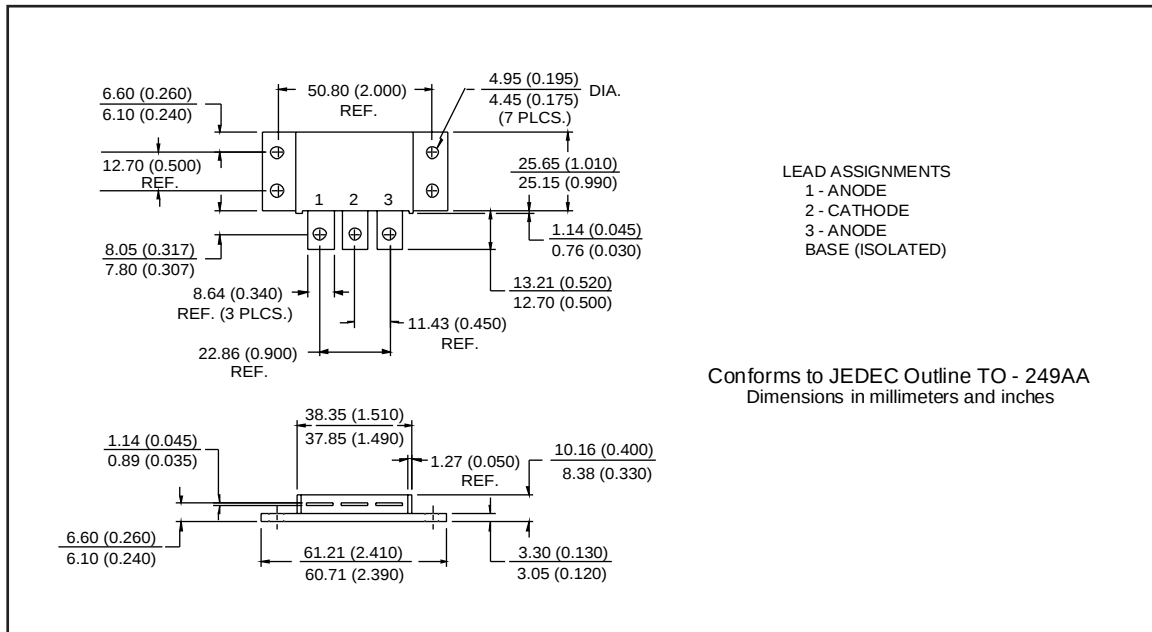
International
IOR Rectifier

Electrical Characteristics (per Leg) @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
V_{BR}	Cathode Anode Breakdown Voltage	600	—	—	V	$I_R = 100\mu\text{A}$
V_{FM}	Max Forward Voltage	—	1.3	1.5	V	$I_F = 30\text{A}$
		—	1.4	1.7		$I_F = 60\text{A}$ See Fig. 1
		—	1.1	1.3		$I_F = 30\text{A}, T_J = 125^\circ\text{C}$
I_{RM}	Max Reverse Leakage Current	—	2.0	10	μA	$V_R = V_R$ Rated See Fig. 2
		—	0.50	2.0	mA	$T_J = 125^\circ\text{C}, V_R = 480\text{V}$
C_T	Junction Capacitance	—	68	100	pF	$V_R = 200\text{V}$ See Fig. 3
L_S	Series Inductance	—	8.0	—	nH	From terminal hole to terminal hole

Dynamic Recovery Characteristics (per Leg) @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
t_{rr}	Reverse Recovery Time	—	30	—	ns	$I_F = 1.0\text{A}, di_F/dt = 200\text{A}/\mu\text{s}, V_R = 30\text{V}$
t_{rr1}		—	67	100		$T_J = 25^\circ\text{C}$ See Fig. 5
t_{rr2}		—	112	170		$T_J = 125^\circ\text{C}$
I_{RRM1}	Peak Recovery Current	—	6.0	11	A	$T_J = 25^\circ\text{C}$ See Fig. 6
I_{RRM2}		—	9.0	16		$T_J = 125^\circ\text{C}$
Q_{rr1}	Reverse Recovery Charge	—	200	550	nC	$T_J = 25^\circ\text{C}$ See Fig. 7
Q_{rr2}		—	500	1400		$T_J = 125^\circ\text{C}$
$di_{(rec)M}/dt1$	Peak Rate of Fall of Recovery Current	—	250	—	$\text{A}/\mu\text{s}$	$T_J = 25^\circ\text{C}$ See Fig. 8
$di_{(rec)M}/dt2$	During t_b	—	170	—		$T_J = 125^\circ\text{C}$



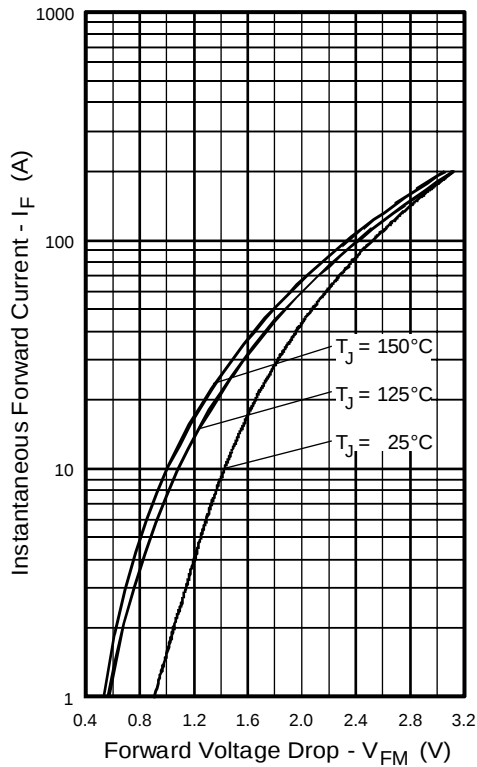


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current, (per Leg)

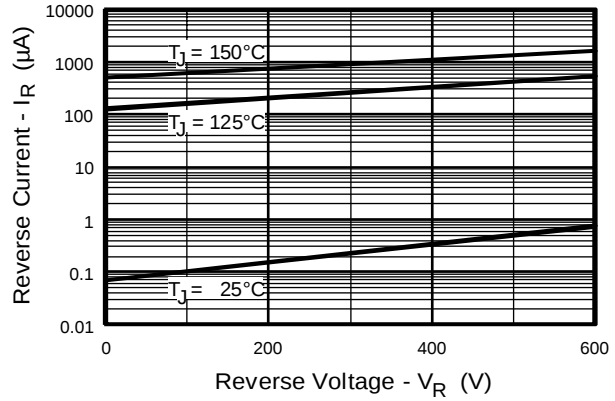


Fig. 2 - Typical Reverse Current vs. Reverse Voltage, (per Leg)

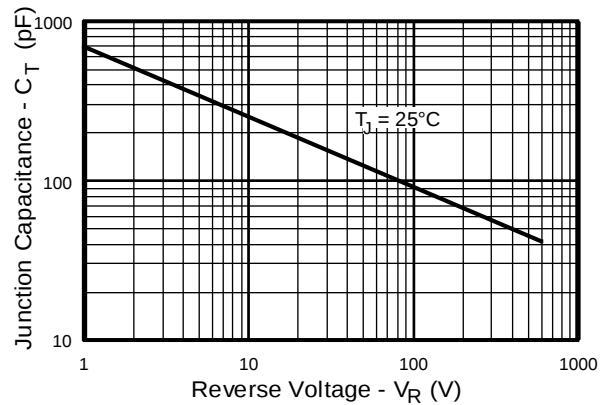


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage, (per Leg)

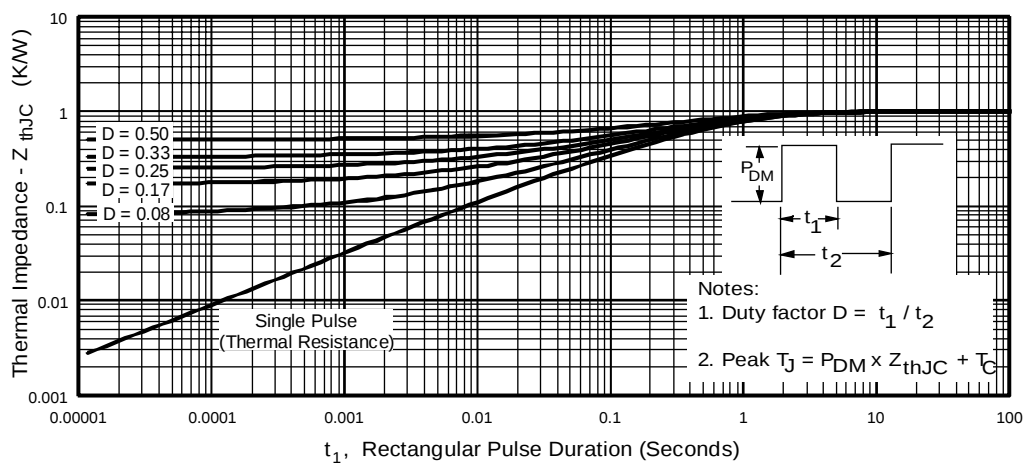


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics, (per Leg)

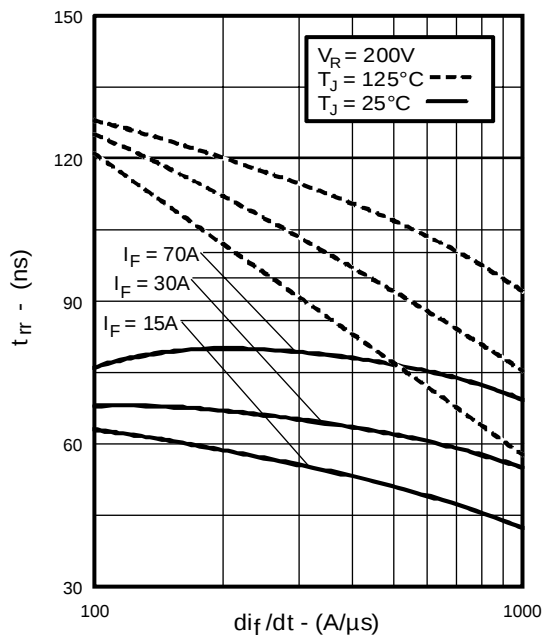


Fig. 5 - Typical Reverse Recovery vs. di_f/dt , (per Leg)

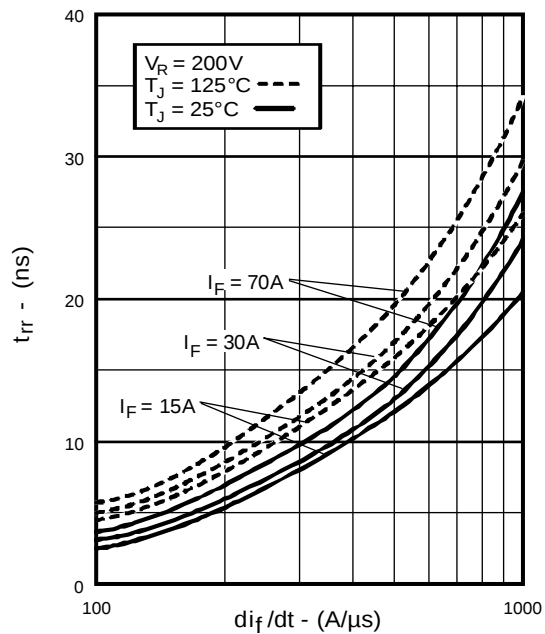


Fig. 6 - Typical Recovery Current vs. di_f/dt , (per Leg)

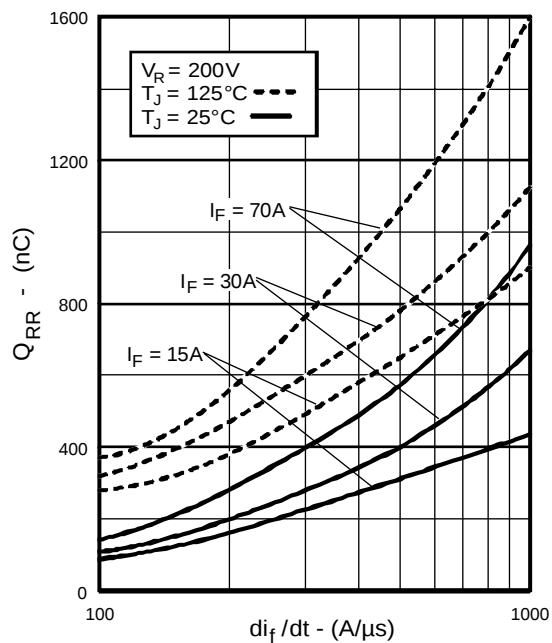


Fig. 7 - Typical Stored Charge vs. di_f/dt , (per Leg)

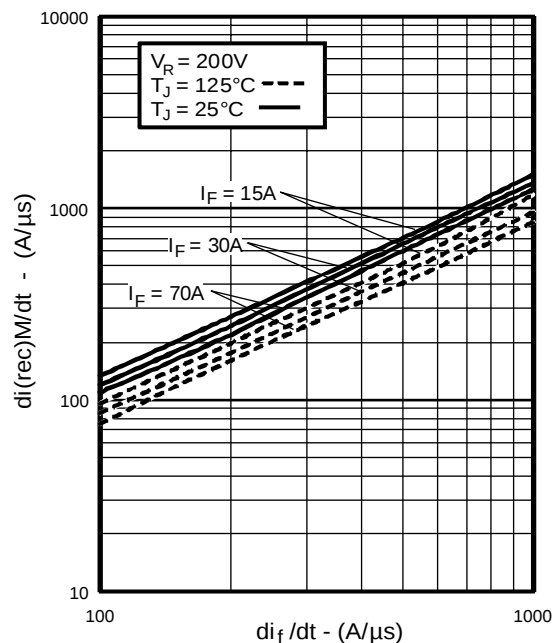


Fig. 8 - Typical $di_{(rec)M}/dt$ vs. di_f/dt , (per Leg)

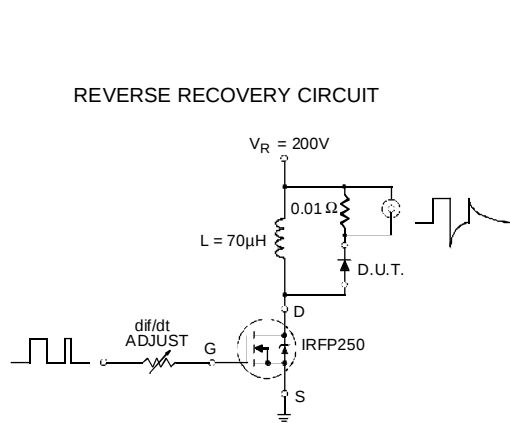


Fig. 9 - Reverse Recovery Parameter Test Circuit

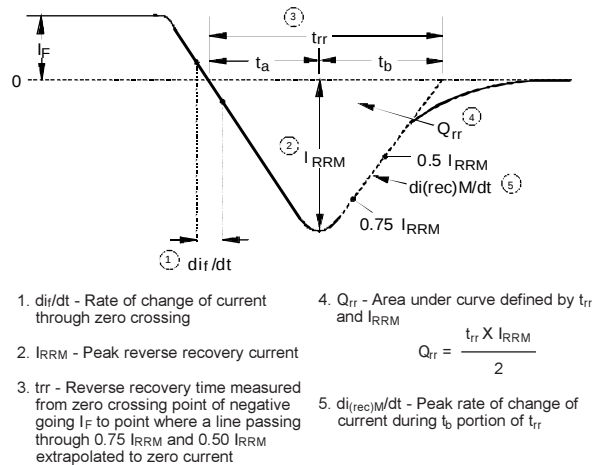


Fig. 10 - Reverse Recovery Waveform and Definitions

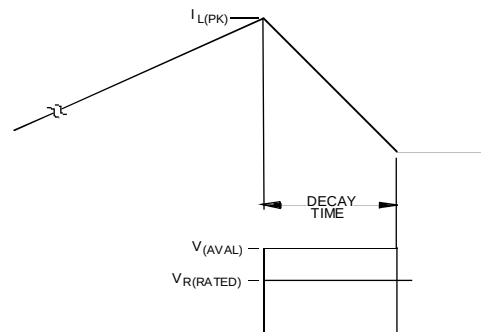
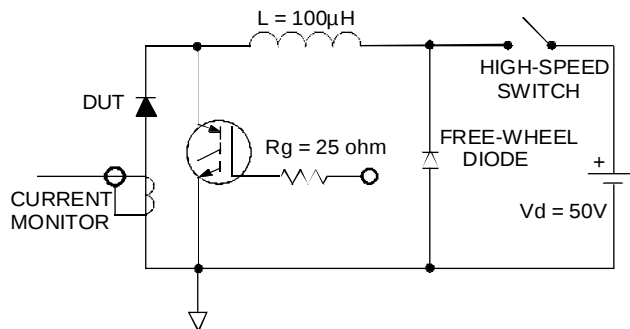


Fig. 11 - Avalanche Test Circuit and Waveforms